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PUBLICATIONS & OTHER RESEARCH OUTPUTS

Publications in refereed journals and proceedings of International Conferences

2018-2021

- [1] Vasileiadis, N., Loukas, P., Karakolis, P., Ioannou-Sougleridis, V., Normand, P., Ntinis, V., Fyrigos, I.-A., Karafyllidis, I., Sirakoulis, G.C., Dimitrakis, P., Multi-level resistance switching and random telegraph noise analysis of nitride based memristors, *Chaos, Solitons and Fractals*, 153, art. no. 111533, 2021.
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